

30V N-Ch Power MOSFET

Feature

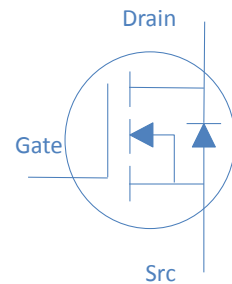
- ◇ High Speed Power Switching, Logic Level
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

| | | | |
|-------------------------|--------------|----|------------|
| V_{DS} | | 30 | V |
| $R_{DS(on),typ}$ | $V_{GS}=10V$ | 30 | m Ω |
| I_D (Silicon Limited) | | 5 | A |

Application

- ◇ Hard Switching and High Speed Circuit
- ◇ DC/DC in Telecoms and Industrial

SOT-23



| Part Number | Package | Marking |
|-------------|---------|---------|
| HTJ350N03 | SOT23 | 1D |

Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ (unless otherwise specified)

| Parameter | Symbol | Conditions | Value | Unit |
|--------------------------------------------|----------------|------------------------|------------|------------------|
| Continuous Drain Current (Silicon Limited) | I_D | $T_A=25^\circ\text{C}$ | 5 | A |
| | | $T_A=70^\circ\text{C}$ | 3.3 | |
| Drain to Source Voltage | V_{DS} | - | 30 | V |
| Gate to Source Voltage | V_{GS} | - | ± 20 | V |
| Pulsed Drain Current | I_{DM} | - | 20 | A |
| Power Dissipation | P_D | $T_A=25^\circ\text{C}$ | 1.04 | W |
| Operating and Storage Temperature | T_J, T_{stg} | - | -55 to 150 | $^\circ\text{C}$ |

Absolute Maximum Ratings

| Parameter | Symbol | Max | Unit |
|-------------------------------------|-----------------|-----|--------------------|
| Thermal Resistance Junction-Ambient | $R_{\theta JA}$ | 120 | $^\circ\text{C/W}$ |

Electrical Characteristics at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)
Static Characteristics

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------------------------------|---------------|--------------------------------------------------|-------|-----|-----------|------------|
| | | | min | typ | max | |
| Drain to Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250\mu A$ | 30 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS}=V_{DS}, I_D=250\mu A$ | 1 | 1.5 | 3.0 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS}=0V, V_{DS}=24V, T_J=25^{\circ}\text{C}$ | - | - | 1 | μA |
| | | $V_{GS}=0V, V_{DS}=20V, T_J=125^{\circ}\text{C}$ | - | - | 10 | |
| Gate to Source Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| Drain to Source on Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=5A$ | - | 30 | 35 | m Ω |
| | | $V_{GS}=4.5V, I_D=4A$ | - | 40 | 50 | |
| Transconductance | g_{fs} | $V_{DS}=5V, I_D=5A$ | - | 11 | - | S |

Dynamic Characteristics

| | | | | | | |
|-------------------------------|--------------|------------------------------------------------|---|-----|---|----|
| Input Capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=10V, f=1\text{MHz}$ | - | 323 | - | pF |
| Output Capacitance | C_{oss} | | - | 75 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 53 | - | |
| Total Gate Charge | Q_g | $V_{DD}=10V, I_D=5A, V_{GS}=10V$ | - | 7.1 | - | nC |
| Gate to Source Charge | Q_{gs} | | - | 1.1 | - | |
| Gate to Drain (Miller) Charge | Q_{gd} | | - | 2.2 | - | |
| Turn on Delay Time | $t_{d(on)}$ | $V_{DD}=15V, I_D=1A, V_{GS}=10V, R_G=6\Omega,$ | - | 8 | - | ns |
| Rise time | t_r | | - | 12 | - | |
| Turn off Delay Time | $t_{d(off)}$ | | - | 28 | - | |
| Fall Time | t_f | | - | 15 | - | |

Reverse Diode Characteristics

| | | | | | | |
|-----------------------|----------|---------------------|---|--|-----|---|
| Diode Forward Voltage | V_{SD} | $V_{GS}=0V, I_F=2A$ | - | | 1.2 | V |
|-----------------------|----------|---------------------|---|--|-----|---|

Fig 1. Typical Output Characteristics

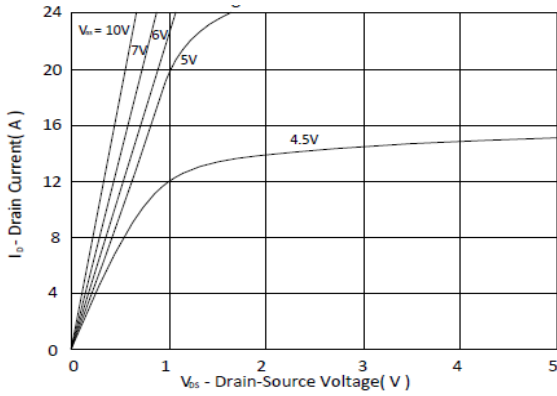


Figure 2. On-Resistance vs. Gate-Source Voltage

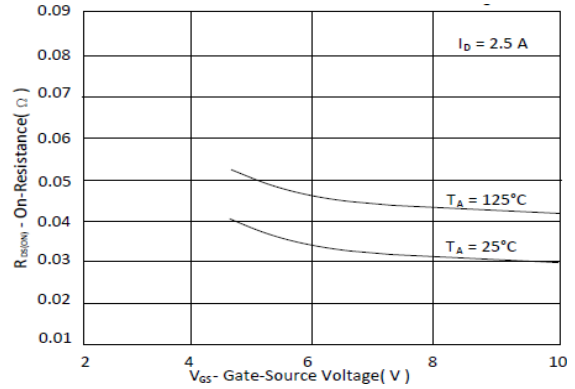


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

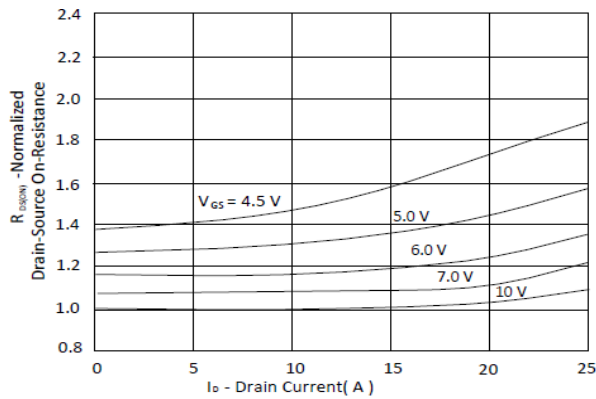


Figure 4. Normalized On-Resistance vs. Junction Temperature

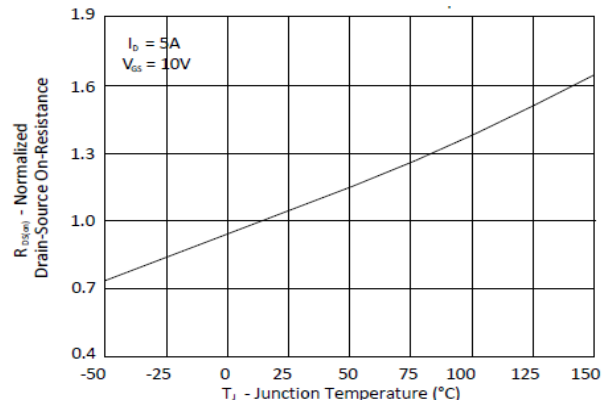


Figure 5. Typical Transfer Characteristics

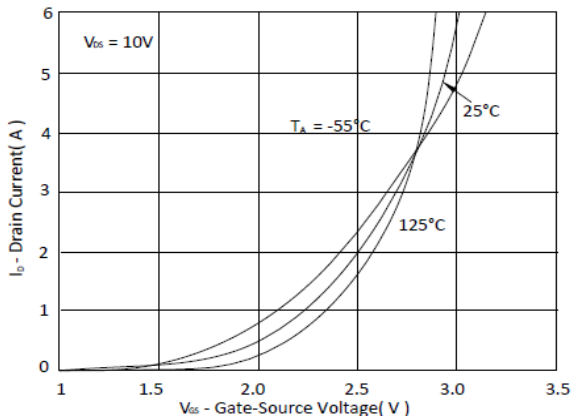


Figure 6. Typical Source-Drain Diode Forward Voltage

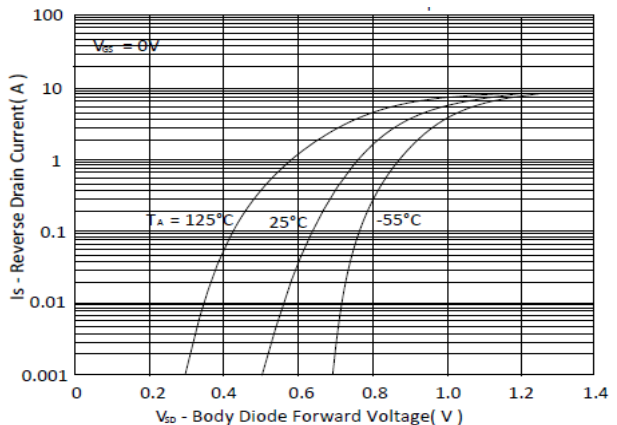


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

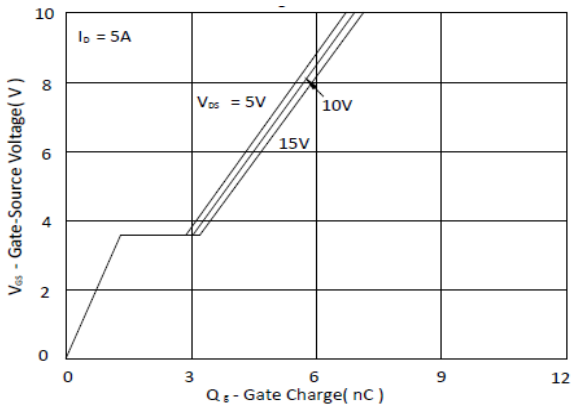


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

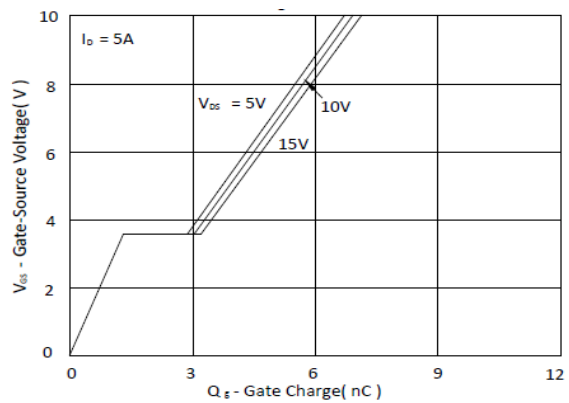


Figure 9. Maximum Safe Operating Area

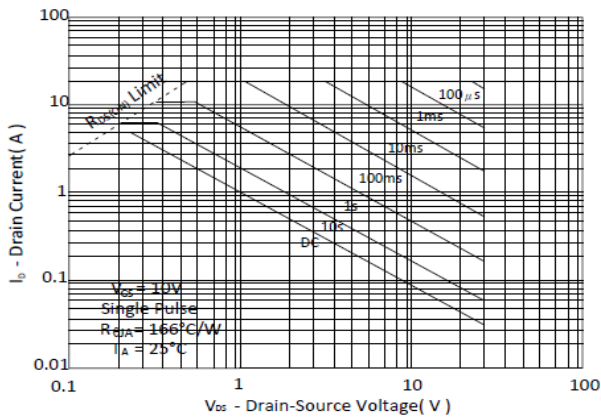


Figure 10. Single Pulse Maximum Power Dissipation

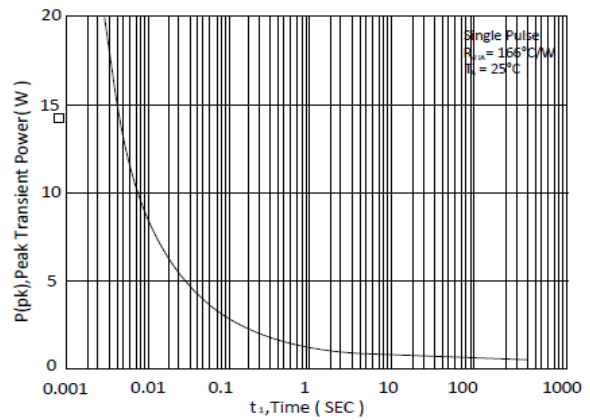
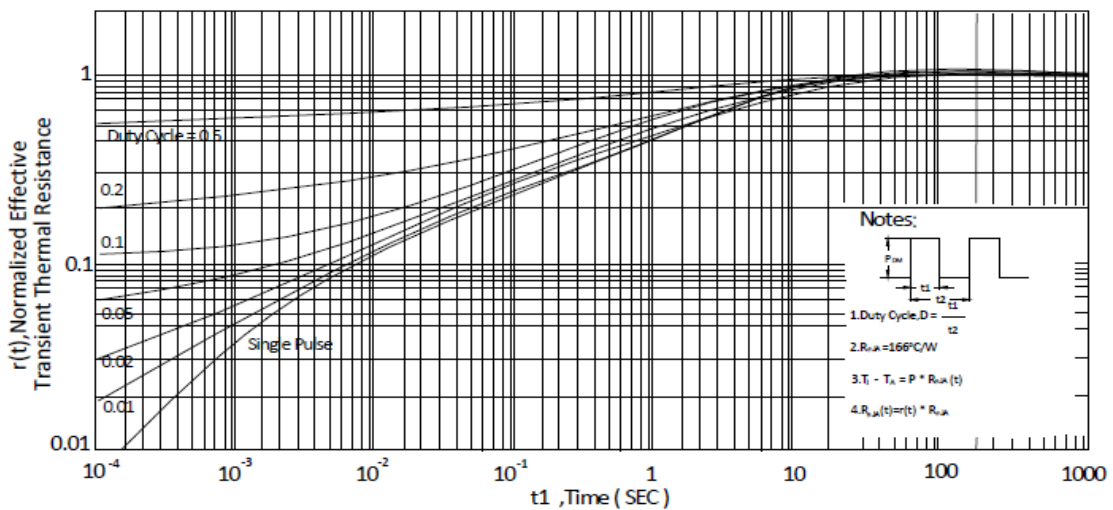
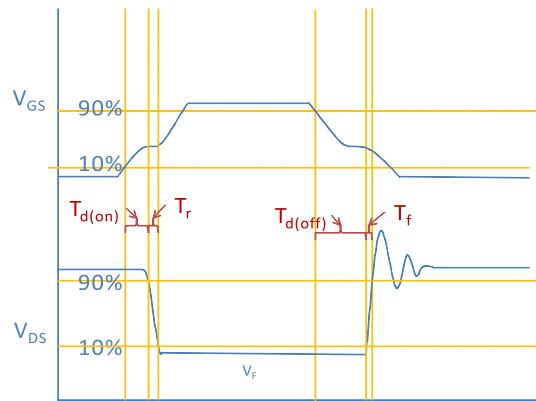
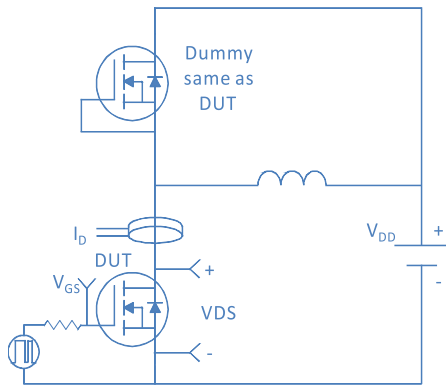


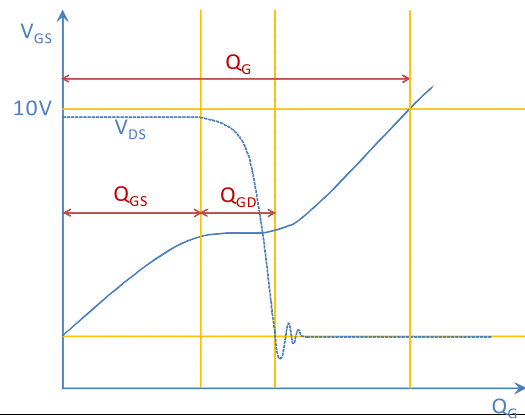
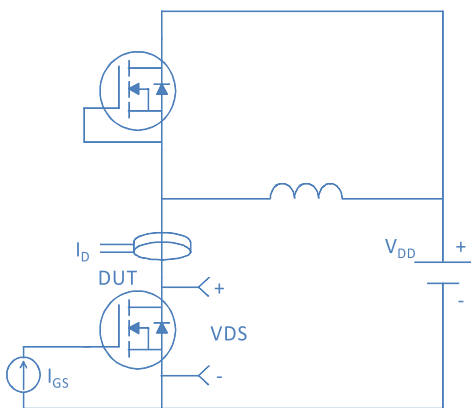
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



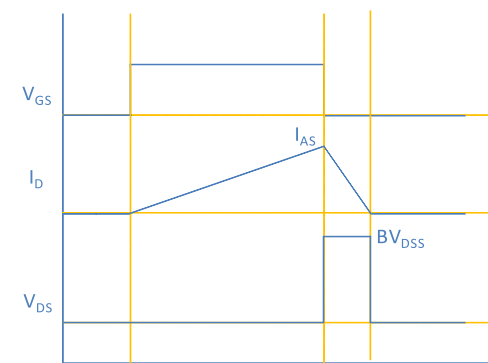
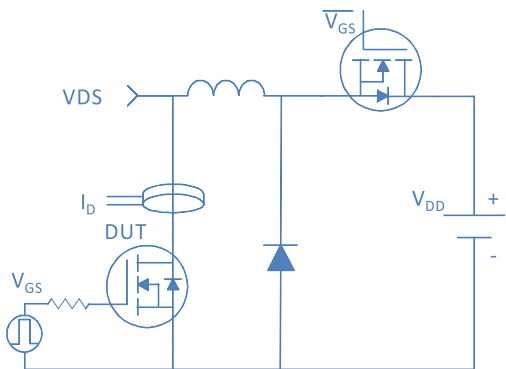
Inductive switching Test



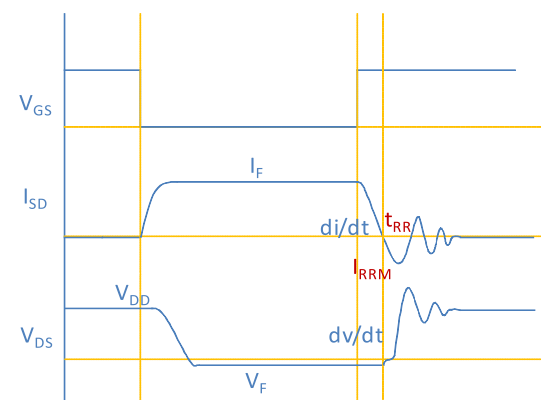
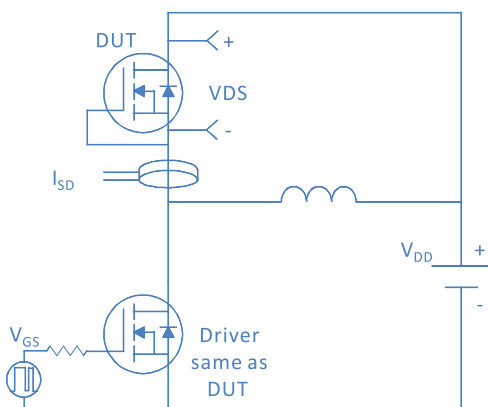
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

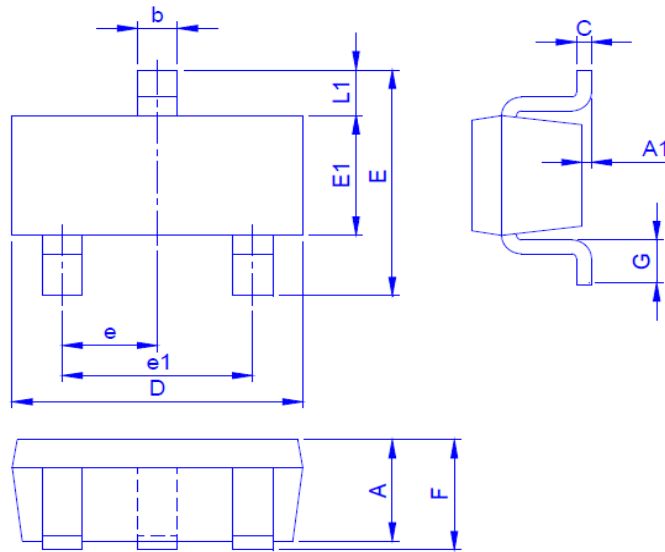


Diode Recovery Test



Package Outline

SOT-23, 3leads



Dimension in mm

| Dimension | A | A1 | b | C | D | E | E1 | e | e1 | F | G | L1 |
|-----------|------|-----|-----|------|------|------|-----|------|-----|------|-----|------|
| Min. | 0.70 | 0 | 0.3 | 0.08 | 2.80 | 2.25 | 1.2 | 0.90 | | 0.80 | 0.3 | 0.50 |
| Typ. | | | | | 2.90 | | | 0.95 | 1.9 | | | |
| Max. | 1.15 | 0.1 | 0.5 | 0.20 | 3.02 | 3.00 | 1.7 | 1.00 | | 1.25 | 0.6 | 0.75 |